

Part IIB 2012 4C15 MEMS Design

$$(a) \quad \delta = b/2\sqrt{km} = 10^{-4}/2\sqrt{10 \times 10^{-7}} = 0.05$$

Mechanics  
Data Book

$$f_r = f_n \sqrt{1 - 2\delta^2}$$

$$= \frac{L}{2\pi} \sqrt{\frac{10}{10^{-7}}} \sqrt{1 - 2(0.05)^2}$$

$$= 1.59 \text{ kHz}$$

$$\omega_r = 9.97 \text{ s}^{-1}$$

$$\Delta x = \frac{a}{\omega_r^2} = \frac{9.81}{(9.97)^2} = 98.6 \times 10^{-9} \text{ m} = 98.6 \text{ nm}$$

ie. 1g

$$(b) \quad C = N \times C_u$$

N = no of unit cells

C<sub>u</sub> = capacitance of each cell

$$C_u = \frac{8.85 \times 10^{-12} \times 10 \times 750 \times 10^{-6}}{2} = 33.1 \times 10^{-15} \text{ F}$$

$$N = \frac{2 \times 2.5 \times 10^{-3}}{44 \times 10^{-6}} \Rightarrow 112$$

2 sides

$$\therefore C = 112 \times 33.1 \times 10^{-15} \Rightarrow 3.77 \text{ pF}$$

$$(c) \quad \frac{\Delta C}{C} = \frac{2x}{g_{\text{gap}}} = \frac{2 \times 98.6 \times 10^{-9}}{2 \times 10^{-6}} = 98.6 \times 10^{-3}$$

ie. 9.86%

$$(d) \quad \bar{F}_n = \sqrt{4k_B T x b} = \sqrt{4 \times 1.38 \times 10^{-23} \times 300 \times 10^{-4}}$$

$$\Rightarrow 1.287 \times 10^{-12} \text{ N}/\sqrt{\text{Hz}}$$

$$\frac{\bar{F}_n}{k} = \bar{x}_n = \frac{1.287 \times 10^{-12}}{10} = 1.29 \times 10^{-13} \text{ m}/\sqrt{\text{Hz}}$$

$$\therefore \bar{a}_n = \frac{1.29 \times 10^{-13}}{98.6 \times 10^{-9}} \text{ g}/\sqrt{\text{Hz}} = 1.31 \times 10^{-6} \text{ g}/\sqrt{\text{Hz}}$$

from (a) ~

$$\text{or } 1.28 \times 10^{-5} \text{ m s}^{-2}/\sqrt{\text{Hz}}$$

(e) It is usually assumed that increasing the probe mass area & structural thickness and reducing the gap  $g$  improves the noise equivalent resolution. However to first order, sensitivity is independent of structural thickness and gap and tuning these parameters may actually increase the fluidic damping and hence the thermo-mechanical noise equivalent acceleration.

Tuning these parameters in the opposite direction will result in lower capacitance and therefore sensitivity that may degrade the electronic noise equivalent resolution.

Increasing the overall area may be beneficial in increasing mechanical sensitivity - by reducing the natural frequency and also allowing for increased capacitance thereby reducing the electronic noise equivalent rate. However this could also lead to increased fluidic damping via Couette drag against the substrate. A process level option to reduce such fluidic dissipation is vacuum packaging.

### Examiner comments

Generally well done and mistakes more often numeric or algebraic rather than conceptual. Rather concerning was the fact that several candidates forget about  $2\pi$  when specifying frequency in Hz.

2. (a)

$$F = \underbrace{\frac{\epsilon_0 t V^2}{2g_0}}_{\text{combarine}} + \underbrace{\frac{\epsilon_0 A V^2}{2(g_0 - x)^2}}_{\text{1/el plate}} \quad \text{for derivation see Lecture notes}$$

(b)  $k_e = \frac{\partial F}{\partial x} = \frac{-2 \cdot \epsilon_0 A V^2}{2(g_0 - x)^3} = \frac{\epsilon_0 A V^2}{(g_0 - x)^3}$

(c) at pull-in force balance  $kx = \frac{\epsilon_0 t V^2}{2g_0} + \frac{\epsilon_0 A V^2}{2(g_0 - x)^2} \quad \text{--- ①}$

But also  $k_m = k_e = k$

ie.  $\frac{\epsilon_0 A V^2}{(g_0 - x)^3} = k \quad \text{--- ②}$

Substituting for  $k$  in ①

$$\frac{\epsilon_0 A V^2 \cdot x}{(g_0 - x)^3} = \frac{\epsilon_0 t V^2}{2g_0} + \frac{\epsilon_0 A V^2}{2(g_0 - x)^2}$$

ie.  $2g_0 x A = t(g_0 - x)^3 + A g_0 (g_0 - x)$

Now put  $z = g_0 - x$  ie.  $x = g_0 - z$

$$2g_0 A (g_0 - z) = t z^3 + A g_0 z$$

ie.  $z^3 + \frac{3A g_0}{t} z = \frac{2g_0^2 A}{t}$

So using provided hint

$$z_{PI} = \left\{ \frac{g_0^2 A}{t} + \sqrt{\frac{g_0^3 A^3}{t^3} + \frac{g_0^4 A^2}{t^2}} \right\}^{1/3} + \left\{ \frac{g_0^2 A}{t} - \sqrt{\frac{g_0^3 A^3}{t^3} + \frac{g_0^4 A^2}{t^2}} \right\}^{1/3}$$

writing as  $z_{PI} = (a + \sqrt{b})^{1/3} + (a - \sqrt{b})^{1/3}$

$a = \frac{g_0^2 A}{t} \quad \sqrt{b} = \sqrt{\dots}$

$$\begin{aligned} \frac{z_{PI}^3}{z_{PI}} &= (a + \sqrt{b}) + 3(a + \sqrt{b})^{2/3}(a - \sqrt{b})^{1/3} + 3(a + \sqrt{b})^{1/3}(a - \sqrt{b})^{2/3} + (a - \sqrt{b}) \\ &= 2a + 3(a + \sqrt{b})^{1/3}(a - \sqrt{b})^{1/3} \{ (a + \sqrt{b})^{2/3} + (a - \sqrt{b})^{2/3} \} \end{aligned}$$

i.e.  $z_{PI}^3 \Rightarrow 2a + 3(a^2 - b)^{1/3} \cdot z_{PI}$

But from (2)  $z_{PI}^3 = \frac{\epsilon_0 A V_{PI}^2}{k}$

$$\therefore \frac{\epsilon_0 A V_{PI}^2}{k} = 2a + 3(a^2 - b)^{1/3} z_{PI}$$

Now substitute for  $a$  &  $b$ ,  $a = \frac{q_p^2 A}{\epsilon}$ ;  $b = \frac{q_p^3 A^2}{\epsilon^2} + \frac{q_p^4 A^2}{\epsilon^2}$

$$\therefore \frac{\epsilon_0 A V_{PI}^2}{k} = \frac{2q_p^2 A}{\epsilon} + 3 \left\{ \frac{q_p^2 A^2}{\epsilon^2} - \frac{q_p^3 A^2}{\epsilon^2} - \frac{q_p^4 A^2}{\epsilon^2} \right\}^{1/3} z_{PI}$$

$$\therefore \frac{\epsilon_0 A V_{PI}^2}{k} = \frac{2q_p^2 A}{\epsilon} - \frac{3q_p A}{\epsilon}$$

$$\therefore V_{PI}^2 = \frac{2kq_p^2}{\epsilon_0 \epsilon} \left\{ 1 - \frac{3z_{PI}}{q_p} \right\}$$

(d) System provides advantages of both comb drive and parallel plate actuators. The comb drive allows for large displacements with relatively linear response. While the force generated from a parallel plate actuator is highly non-linear the force density, i.e. force per unit area, is much larger than a comb drive. A design compromise is therefore possible by trading relative areas.

However, the system is still limited by the 'pull-in instability' for voltage controlled operation - so approximates to a parallel plate actuator with improved linearity and added voltage.

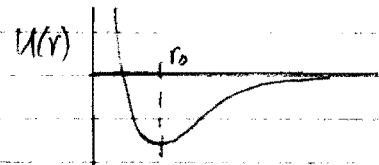
Examiner's comments: candidates invariably avoided rather than derived the expressions in (a). Most candidates got to the cubic, if not its solution & so gained reasonable credit for (c).

3 (a) The force between two atoms has two components. A short range repulsive force and a longer range attractive component.

When two atoms are brought together their electron clouds overlap - as this is energetically unfavourable a repulsive force is generated arising from the Pauli exclusion principle. The essential characteristic is that its magnitude rises very steeply as separation distance  $r$  falls. Typically the interaction energy varies with  $r^{-12}$ .

The force of attraction is known generically as the van der Waals force and can arise from a number of sources. Its potential too falls off with distance  $r$  but less steeply, typically with  $r^{-6}$ .

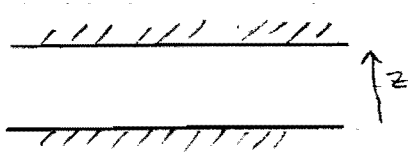
Hence 
$$U(r) = -\frac{C}{r^6} + \frac{D}{r^{12}}$$
 potential



For a fuller discussion of the origin of these terms see the relevant sections of:

- Isvarlachvili J 'Intermolecular & Surface Forces' L6287
- Mate CM 'Tribology on the small scale' RP182
- Mangis D 'Contact Adhesion & Rupture of Elastic Solids' JJ330

(b) Considering only attractive or non-retarded term and integrating for two parallel planes of atoms provides the quoted result. This was first done by Hamaker about 80 yrs ago.



$$U(z) = -\frac{A}{12\pi z^2}$$

$$\text{But } F = -\frac{dU(z)}{dz} = \frac{A}{6\pi z^3}$$

Consider unit area

$$\begin{aligned} \text{But } w &= \int_{h_0}^{\infty} F dz = \frac{A}{6\pi} \int_{h_0}^{\infty} z^{-3} dz = \left[ -\frac{A}{12\pi z^2} \right]_{h_0}^{\infty} \\ &= \frac{A}{12\pi h_0^2} \end{aligned}$$

Note that since  $F = -\frac{dU(z)}{dz}$

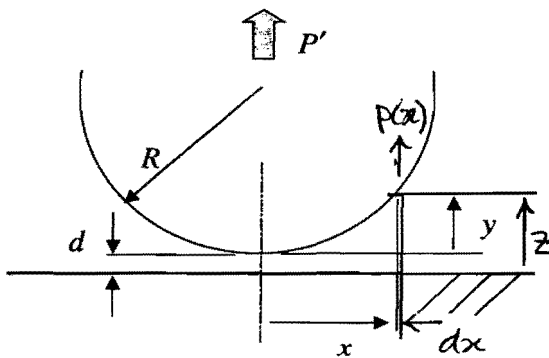
$$\text{and } w = \int_{h_0}^{\infty} F dz \quad w = -\int_{h_0}^{\infty} dU(z)$$

$$= -U(h_0) = \frac{A}{12\pi h_0^2}$$

for any function of  $U(z)$

(c) The Derjaguin approximation is a geometric argument which allows the force law between two curved surfaces to be expressed in terms of the interaction energy between two planar surfaces. The demonstration of this relies relies on the fact that the radius (or radii) of curvature of the convex body are large compared to the separation of the surfaces and thus at a given distance from the point of nearest approach can be in essence parallel.

(d)



$$\text{If } y = \frac{x^2}{2R}$$

'usual' parabolic approx to circle

$$dP' = p(z) dx \times 2$$

(2 sides) per unit length

$$\text{But } z = d + y$$

$$\therefore dz = dy = \frac{2x}{2R} dx$$

$$\text{i.e. } dz = \frac{x}{R} dx$$

$$\therefore dP' = 2x \frac{R}{x} p(z) dz$$

$$\text{But } x = \sqrt{2R(z-d)}$$

Now for plane surfaces  $U(z) = -\frac{A}{12\pi z^2}$

$$\text{i.e. } U(z) = -w h_0^2 z^{-2}$$

or treating axial strip as being held to contact face

$$p(z) = -\frac{\partial u(z)}{\partial z} = \frac{2\omega h_0^2}{z^3}$$

$$dP' = 2 \cdot \frac{2\omega h_0^2}{z^3} \cdot \frac{R}{\sqrt{2R(z-d)}} dz$$

per unit length  $\rightarrow P' = 2\omega h_0^2 \sqrt{2R} \int_d^\infty \frac{dz}{z^3(z-d)^{1/2}}$

Consider  $I = \int_d^\infty \frac{dz}{z^3(z-d)^{1/2}}$

if  $z \gg d$  then  $I \approx \int_d^\infty \frac{dz}{z^{7/2}} = -\left[\frac{2}{5} z^{-5/2}\right]_d^\infty = \frac{2}{5d^{5/2}}$

hence  $P' = 2\omega h_0^2 \sqrt{2R} \cdot \frac{2}{5d^{5/2}}$

$$P' = \frac{4\omega h_0^2 \sqrt{2R}}{5d^{5/2}}$$

Quite possible to find analytical solution

to  $I = \int_d^\infty \frac{dz}{z^3(z-d)^{1/2}}$

by substitution  $z-d=y^2$   
then  $dz=2y dy$ , then  $\theta = \tan^{-1} y/a$

hence  $I = \frac{2}{d^{5/2}} \int_0^{\pi/2} \cos^4 \theta d\theta = \frac{3\pi}{16}$

hence  $P' = \omega h_0^2 \sqrt{\frac{2R}{d^5}} \cdot \frac{3\pi}{8}$

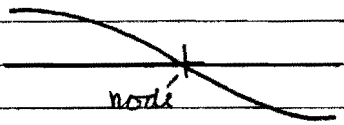
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(e) In addition to problems of surface topography & cleanliness, experimentally maintaining alignment for any nominal line contact would be prohibitively difficult. All such experiments use point contacts - spheres or disks or crossed cylinders.

4 (a)  $\phi$  is high so that  $\omega_n = \sqrt{k/m}$

$$\omega \quad f_n = \frac{1}{2\pi} \sqrt{\frac{\pi^2 EWh}{8L} \times 2} \times \frac{1}{\rho w h L} = \frac{1}{4L} \sqrt{\frac{E}{\rho}}$$

$$\therefore f_n = \frac{1}{4 \times 180 \times 10^{-6}} \sqrt{\frac{160 \times 10^9}{2330}} = \underline{11.5 \text{ MHz}}$$



(b) Helium plate actuator  $F_e = \frac{\epsilon_0 A V_{DC} V_{AC}}{g^2}$

amplitude at resonance,  $X \approx \frac{\phi \cdot F_e}{k}$

$$X = \frac{\phi \epsilon_0 A V_{DC} V_{AC}}{g^2} \times \frac{8L}{\pi^2 EWh}$$

$$= \frac{10^5 \times 8.854 \times 10^{-12} \times 10 \times 8 \times 10^{-12} \times 50 \times 1}{(1 \times 10^{-6})^2} \times \frac{8}{\pi^2} \times \frac{180 \times 10^{-6}}{160 \times 10^9 \times 10 \times 8 \times 10^{-12}}$$

$$= 40.4 \times 10^{-9} \text{ m}$$

$$\approx \underline{40.4 \text{ nm}}$$

$i_m$  motional current =  $\frac{dQ}{dt}$  (from (a)) (from (b))

$$= V_p \frac{dC}{dt} = V_p \frac{d}{dt} \left( \frac{\epsilon_0 A}{g-x} \right) = \frac{V_p \epsilon_0 A}{(g-x)^2} \omega X$$

$g-x = g$  when displacement  $x$ , so when  $x=0$

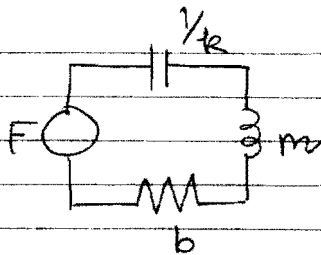
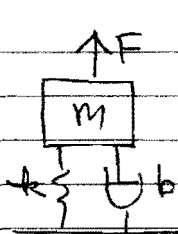
$$i_m = \frac{50 \times 8.85 \times 10^{-12} \times 10 \times 8 \times 10^{-12}}{1 \times 10^{-12}} \times 11.5 \times 10^6 \times 2\pi$$

$$= 1.03 \times 10^{-7} \text{ amp}$$

$$= \underline{0.103 \text{ } \mu\text{amp}}$$

(c) The required expressions can be written down from analogy between a mechanical and an electrical system.





$$k = \frac{\pi^2 E \omega h}{8 L}$$

$$m = \frac{\rho w l h}{2}$$

$$R_m = \frac{b}{\eta^2}, \quad L_m = \frac{m}{\eta^2}, \quad C_m = \frac{\eta^2}{k}$$

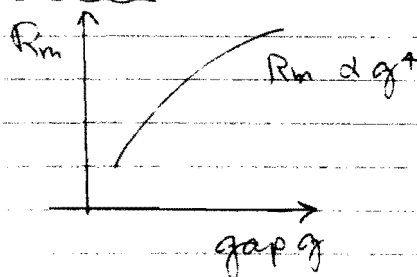
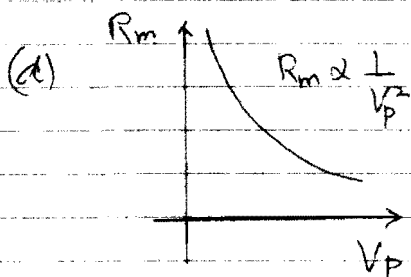
$$\eta = V_p \frac{dc}{dx} = V_p \frac{\epsilon_0 A}{g^2} \quad \text{for asymmetric 1/4 plate}$$

$$\eta = \frac{100 \times 8.854 \times 10^{-12} \times 10 \times 8 \times 10^{-12}}{(1 \times 10^{-6})^2} = 7.08 \times 10^{-8}$$

$$\therefore C_m = \frac{(7.08 \times 10^{-8})^2 \times 8 \times 180 \times 10^{-6}}{\pi^2 \times 160 \times 10^9 \times 10 \times 8 \times 10^{-12}} \Rightarrow 57.1 \times 10^{-21} \text{ F}$$

$$L_m = \frac{2330 \times 10 \times 180 \times 8 \times 10^{-18}}{2 \times (7.08 \times 10^{-8})^2} \Rightarrow 3347 \text{ H}$$

$$R_m = \frac{m \omega r}{\phi \eta^2} = \frac{2330 \times 10 \times 180 \times 8 \times 10^{-18} \times 11.5 \times 10^6 \times \pi}{2 \times 10^5 \times (7.08 \times 10^{-8})^2} = 2.42 \text{ M}\Omega$$



Motional resistance may be minimised by reducing gap  $g$  - however, this reduces the motional amplitude and narrows the onset of non-linearities - or increasing the DC voltage - this usually has a limit either due to nature of process or by pull-in instability. Increasing area through scaling thickness provides some benefit - automatic resonator topologies are also possible.

## Examiner's comments

3. Parts (a) & (b) well done - explanations for Dujardin approximation were sometimes a bit confused involving - erroneously - elasticity and condensation bridges. Elasticity of surfaces is accounted for in either JKR or DMT treatments. The difficulty about evaluating the integral in (d) was appreciated by some candidates.
4. Several candidates either didn't bother about mode shape - or else put nodes at the ends of the free-free beam and an antinode at the centre.

2012 4C15 Answers

- 1 (a) 1.59 kHz 98.6 nm (b) 3.77 pF (c) 9.9% (d)  $1.28 \times 10^{-5} \text{ ms}^{-2}/\sqrt{\text{Hz}}$
2. (a)  $\frac{\epsilon_0 t V^2}{2g_0}$ ,  $\frac{\epsilon_0 A V^2}{2(g_0 - x)^2}$  (b)  $\frac{\epsilon_0 A V^2}{(g_0 - x)^3}$  (c)  $V_{PI}^2 = \frac{2kg_0^2}{\epsilon_0 t} \left\{ 1 - \frac{3z_{PI}}{g_0} \right\}$ ;  $z_{PI}^3 = \frac{\epsilon_0 V_{PI}^2}{k}$
- 3  $P' = \frac{3\pi}{8} wh_0^2 \sqrt{\frac{2R}{d^5}}$
- 4 (a) 11.5 MHz, (b) 40.4 nm 0.103  $\mu\text{amp}$  (c)  $R_m = 2.42 \text{ M}\Omega$ ,  $L_m = 3347 \text{ H}$ ,  
 $C_m = 57.1 \times 10^{-21} \text{ F}$